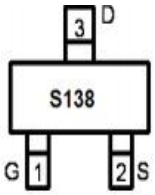
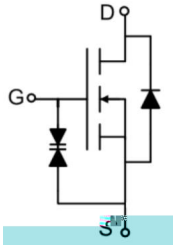
V_{DSS}	50V
$R_{DS}(on)$	3.5Ω(Max)
I_D	0.22A





Advanced MOSFET process technology
Special designed for PWM, load switching and general purpose applications
Ultra low on-resistance with low gate charge
Fast switching and reverse body recovery
150 operating temperature

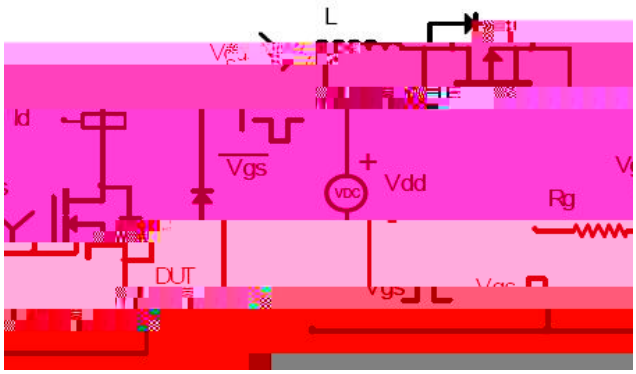
It utilizes the latest processing techniques to achieve the high cell density and reduces the on-resistance with high repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in power switching application and a wide variety of other applications.

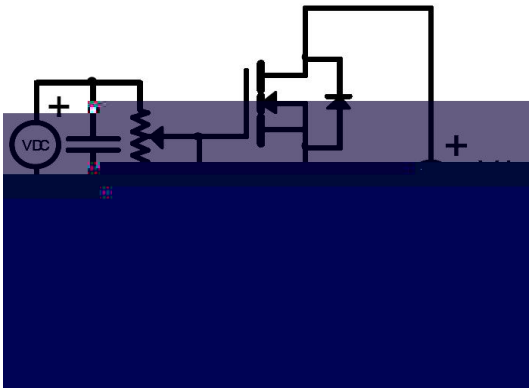
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	0.22	A
I_{DM}	Pulsed Drain Current	0.88	
P_D @T_C = 25°C	Power Dissipation	0.43	W
V_{DS}	Drain-Source Voltage	50	V
V_{GS}	Gate-to-Source Voltage	± 20	V
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C

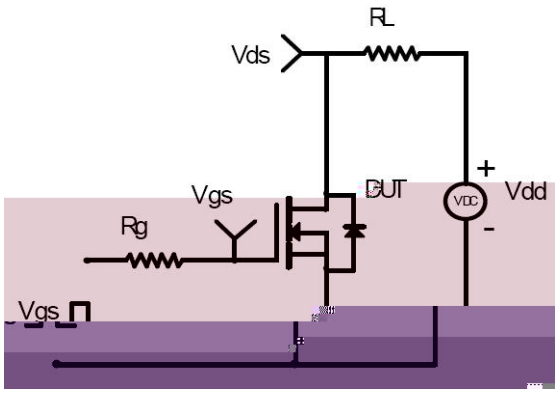
$R_{\theta JA}$	Junction-to-Ambient	—	350	/W

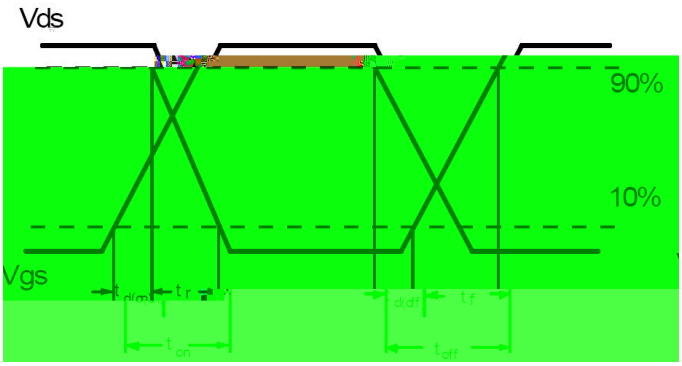
@T_A=25 unless otherwise specified

$V_{(BR)DSS}$	Drain-to-Source breakdown voltage	50	—	—	V	V_{GS} = 0V, I_D = 250μA
$R_{DS(on)}$	Static Drain-to-Source on-resis					







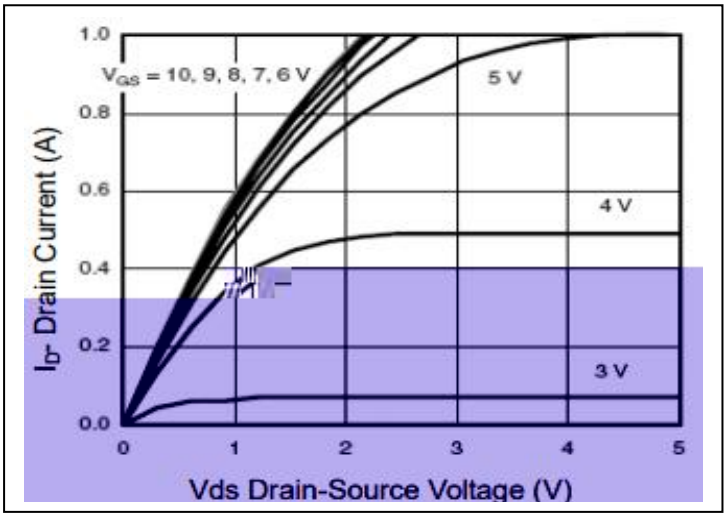


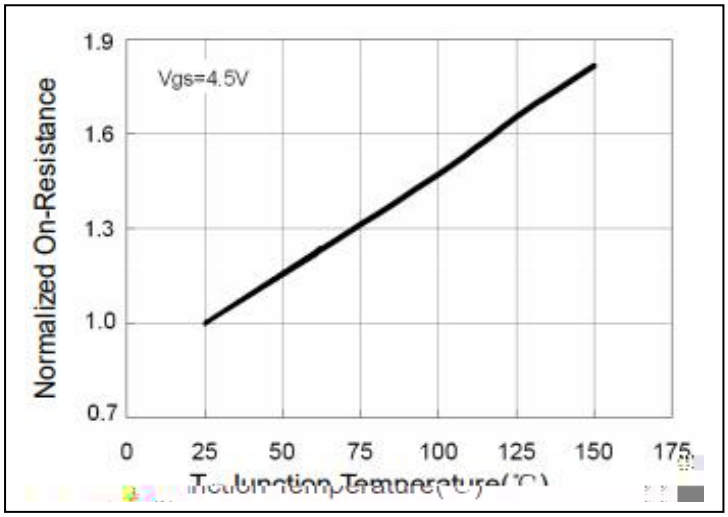
Calculated continuous current based on maximum allowable junction temperature.

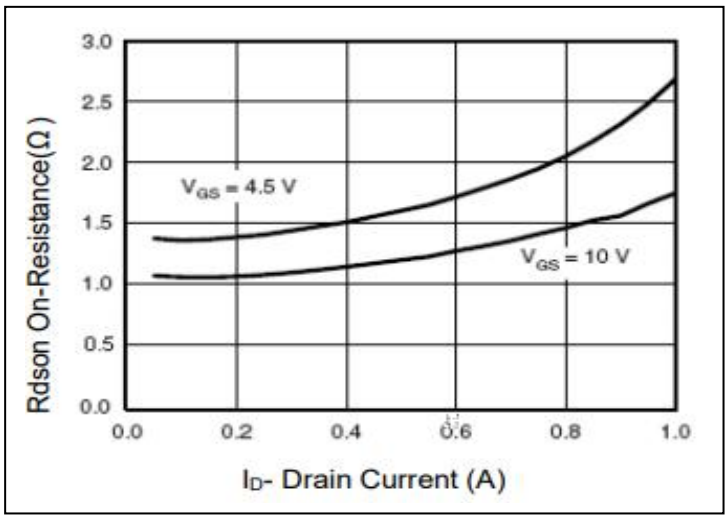
Repetitive rating; pulse width limited by max. junction temperature.

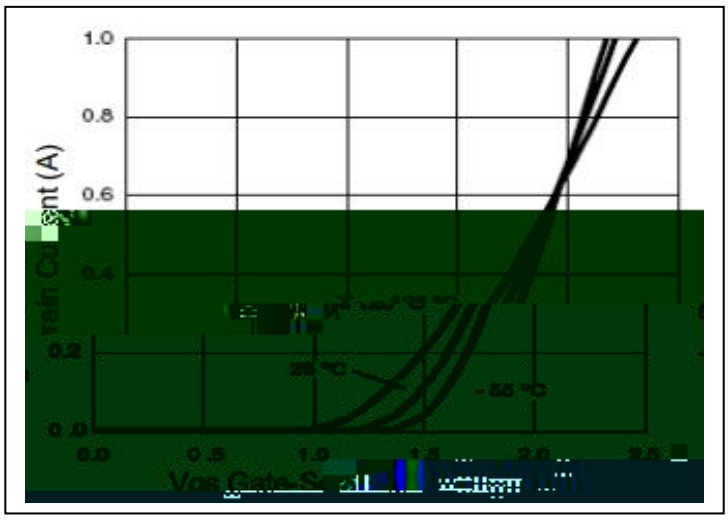
The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.

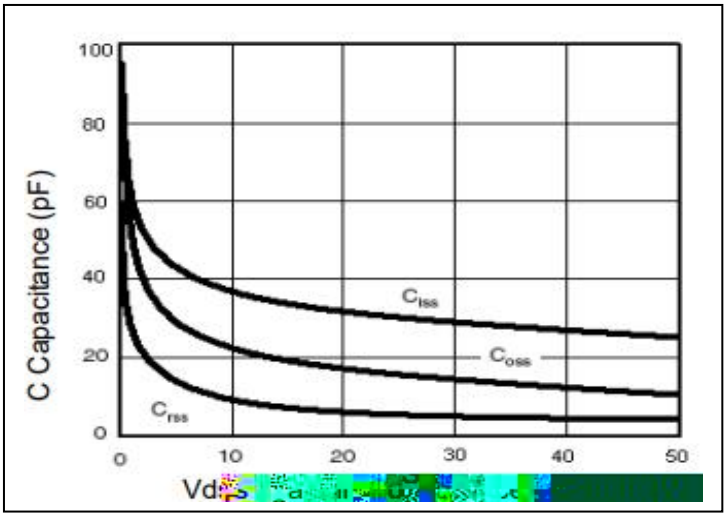
The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with TA =25

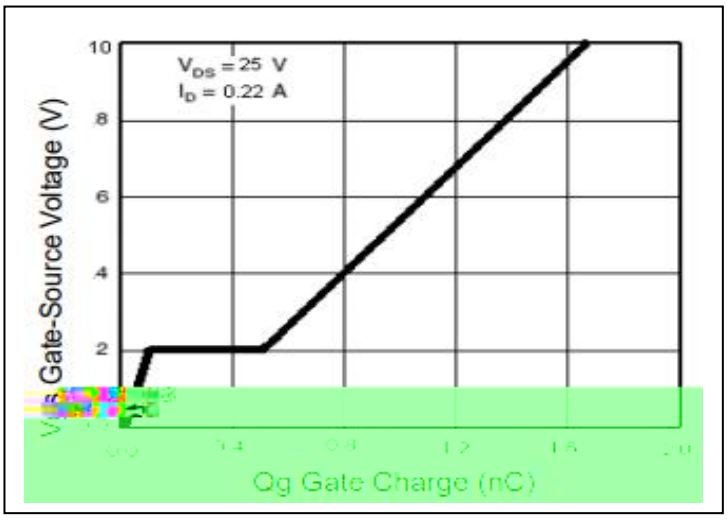

V_{GS} = 10, 9, 8, 7, 6 V
5 V
4 V
3 V
I_D- Drain Current (A)
Vds Drain-Source Voltage (V)

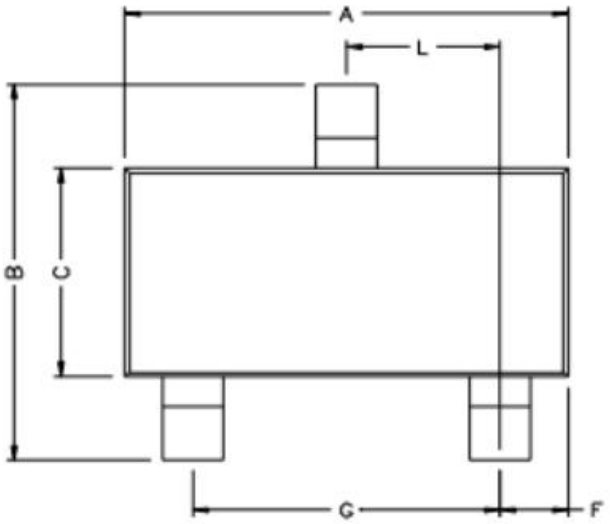

Vgs=4.5V
Normalized On-Resistance


V_{GS} = 4.5 V
V_{GS} = 10 V
Rdson On-Resistance(Ω)
I_D- Drain Current (A)


-55 °C


C_{iss}
C_{oss}
C_{rss}
C Capacitance (pF)


V_{DS} = 25 V
I_D = 0.22 A
Vgs Gate-Source Voltage (V)
Qg Gate Charge (nC)



REF.	Millimeter		REF.	Millimete	
	Min.	Max.		Min.	Max.
A	2.80	3.00	G	1.80	2.00
B	2.30	2.50	H	0.90	1.1
C	1.20	1.40	K	0.10	0.20
D	0.30	0.50	J	0.35	0.70
E	0	0.10	L	0.92	0.98
F	0.45	0.55	M	0°	10°

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